

SILICON TRANSISTOR ARRAY

μ PA1453

PNP SILICON POWER TRANSISTOR ARRAY HIGH SPEED SWITCHING USE INDUSTRIAL USE

DESCRIPTION

The μ PA1453 is PNP silicon epitaxial Power Transistor Array that built in 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- · Easy mount by 0.1 inch of terminal interval.
- High hre. Low Vce(sat).
 hre = 100 to 400 (at Ic = -2 A)
 Vce(sat) = -0.3 V MAX. (at Ic = -2 A)

ORDERING INFORMATION

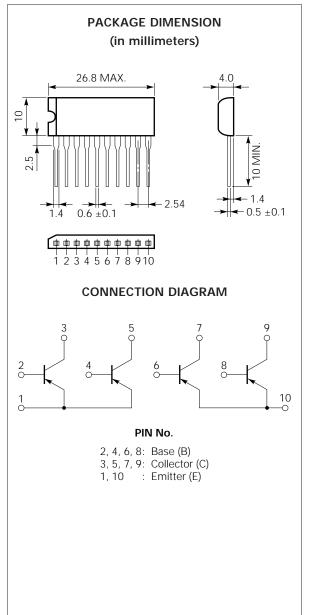
| Part Number | Package | Quality Grade | | |
|-------------|------------|---------------|--|--|
| μPA1453H | 10 Pin SIP | Standard | | |

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

| Collector to Base Voltage | Vсво | -60 | V |
|------------------------------|---------------------|---------|--------|
| Collector to Emitter Voltage | VCEO | -60 | V |
| Emitter to Base Voltage | VEBO | -7 | V |
| Collector Current (DC) | Ic(DC) | -5 | A/unit |
| Collector Current (pulse) | Ic(pulse)* | -10 | A/unit |
| Base Current (DC) | I _{B(DC)} | -1.0 | A/unit |
| Total Power Dissipation | P _{T1} ** | 3.5 | W |
| Total Power Dissipation | P _{T2} *** | 28 | W |
| Junction Temperature | Tj | 150 | .C |
| Storage Temperature | Tstg -55 | to +150 |) °C |

- * PW \leq 300 μ s, Duty Cycle \leq 10 %
- ** 4 Circuits, Ta = 25 °C
- *** 4 Circuits, Tc = 25 °C



The information in this document is subject to change without notice.

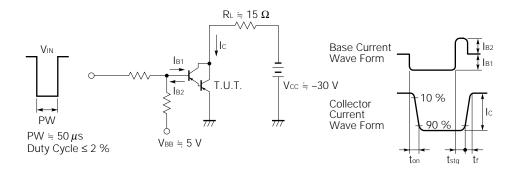


ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|------------------------------|------------------------|------|------|------|------|---|
| Collector Leakage Current | Ісво | | | -10 | μΑ | Vcb = -50 V, IE = 0 |
| Emitter Leakage Current | Ієво | | | -10 | μΑ | V _{EB} = -5 V, I _C = 0 |
| DC Current Gain | h _{FE1} * | 60 | 220 | | _ | Vce = -1 V, Ic = -0.1 A |
| DC Current Gain | h _{FE2} * | 100 | 220 | 400 | _ | Vce = -1 V, Ic = -2 A |
| DC Current Gain | h _{FE3} * | 50 | 100 | | | Vce = -2 V, Ic = -5 A |
| Collector Saturation Voltage | VCE(sat) * | | -0.2 | -0.3 | V | Ic = -2 A, I _B = -0.2 A |
| Base Saturation Voltage | V _{BE(sat)} * | | -0.9 | -1.2 | V | Ic = -2 A, I _B = -0.2 A |
| Turn On Time | ton | | | 1 | μs | Ic = -2 A |
| Storage Time | tstg | | | 2.5 | μs | $I_{B1} = -I_{B2} = -0.2 \text{ A}$ $V_{CC} \doteqdot -30 \text{ V}, \text{ RL} \doteqdot 15 \Omega$ See test circuit |
| Fall Time | tr | | | 1 | μs | |

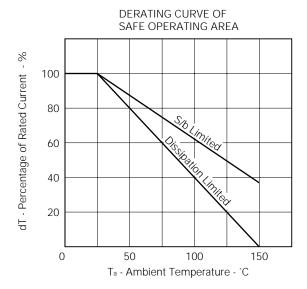
^{*} PW \leq 350 μ s, Duty Cycle \leq 2 % / pulsed

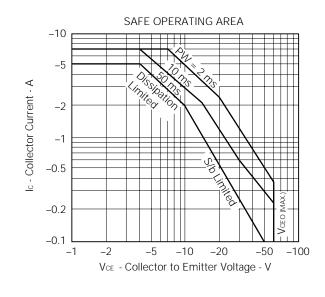
SWITCHING TIME TEST CIRCUIT



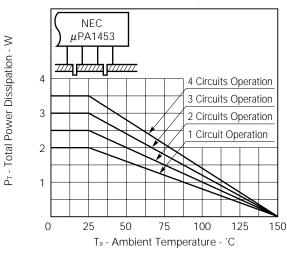


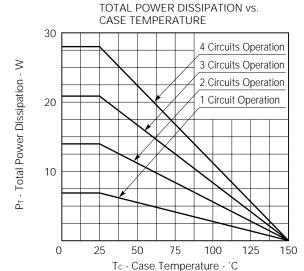
TYPICAL CHARACTERISTICS (Ta = 25 °C)



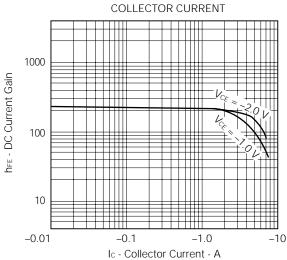


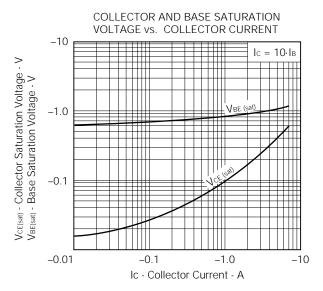




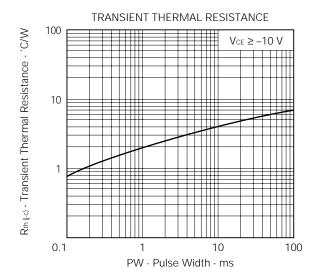


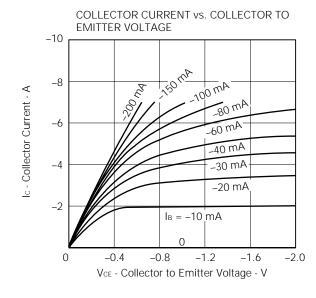
DC CURRENT GAIN vs.

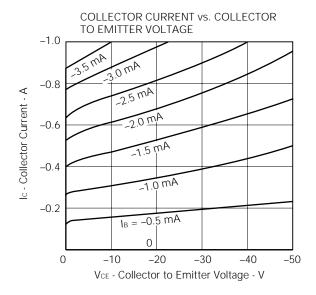


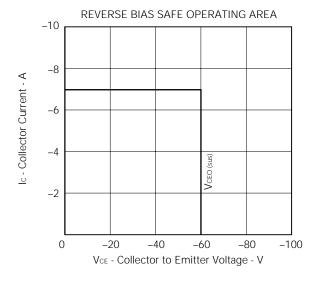














REFERENCE

| Document Name | Document No. |
|--|--------------|
| NEC semiconductor device reliability/quality control system. | TEI-1202 |
| Quality grade on NEC semiconductor devices. | IEI-1209 |
| Semiconductor device mounting technology manual. | IEI-1207 |
| Semiconductor device package manual. | IEI-1213 |
| Guide to quality assurance for semiconductor devices. | MEI-1202 |
| Semiconductor selection guide. | MF-1134 |

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